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Volume A 31 · 1983

Springer-Verlag
Berlin Heidelberg New York Tokyo

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Springer-Verlag Berlin Heidelberg New York Tokyo
Printers: Brühlsche Universitätsdruckerei, Giessen
Printed in Germany © by Springer-Verlag Berlin · Heidelberg 1983

Applied Physics A Solids and Surfaces
© Springer-Verlag 1983

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